



Yujiro Naruse was born in Kanagawa, Japan, on November 30, 1951.

He received the B.E., M.E. and Ph.D. degrees in electronics engineering from the University of Tokyo, Japan, in 1975, 1977, and 1989, respectively. The doctor thesis is on “Silicon X-ray sensors for medical applications” which was performed in the Research and Development Center of Toshiba Corporation, Kawasaki, Japan.

In 1977, he joined the Research and Development Center of Toshiba Corporation, where he worked on silicon x-ray sensors and infrared image sensors.

From September 1983 to February 1985 he studied at Stanford University as a Visiting Scholar in the Department of Electrical Engineering, where he researched on implantable bio-telemetry sensors.

From April 1993 to June 1994 he headed the Advanced Devices group in the Research and Development Center of Toshiba Corporation.

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In October 2005, he was assigned to be a Senior Fellow at the Center for Research and Development Strategy of Japan Science and Technology Agency on leave from Toshiba R&D Center. In January 2007, he was assigned to be a Director for Nanotechnology, Materials and Monodzukuri Technology at the Cabinet Office in Japan.

He is currently a visiting Professor of Center for the Promotion of Research in Nanoscience and Nanotechnology at Osaka University.

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